

YJ Planar Schottky Barrier Diode Die Specification

60V 10A, 87mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB087M060AS-280A

Main Products Characterstics

Maximum Ratings

Symbol	Value
I_F	10 A
V_R	60 V
T_J	175 °C
T_{stg}	250 °C
t_{stg}	1000 h

Static Electrical Characteristics (Ta = 25°C)

Symbol	Value
$I_F = 10\text{ A}$	$V_F \leq 1.0\text{ V}$
$V_R = 60\text{ V}$	$I_{RR} \leq 2\text{ mA}$
$V_F = 1.0\text{ V}$	$I_{RR} \leq 2\text{ mA}$
$I_F = 10\text{ A}$	$r_{FS} \leq 2\text{ m}\Omega$
$V_R = 60\text{ V}$	$C_{JS} \leq 10\text{ pF}$

Device Schematics and Outline Drawing

Die Thickness *	87mil
Die Size **	1.0mm x 1.0mm
Top Metal Pad	0.5mm x 0.5mm
Active Area	0.4mm x 0.4mm
Top Metal	0.5mm x 0.5mm